

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
PEATMAN, WILLIAM C., et al.

Application No.: 09/592349

Filed: 6/12/2000

Docket No.: SC11100ZP

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Patent No.: 6821829

Issue Date: 11/23/2004

Examiner: Douglass Wille

Group Art Unit: 2814

Title: METHOD OF MANUFACTURING A SEMICONDUCTOR COMPONENT AND
SEMICONDUCTOR COMPONENT THEREOF

Certificate of Submission

I hereby certify that this correspondence is being submitted to
the U.S.P.T.O., Alexandria, VA.

___ Addressed per C.F.R. § 1.1(a) and deposited with the
United States Postal Service with sufficient postage as first
class mail.

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X Submitted electronically via EFS in accordance with
"Legal Framework for EFS Web".

9.20.06
Date of Submission
Signature
Pat Thomas
Printed Name of Person Signing Certificate

Commissioner for Patents
Alexandria, VA 22313

SUBMISSION OF CERTIFICATE OF CORRECTION

Dear Commissioner:

Enclosed is a Certificate of Correction listing error(s) in the subject patent. Please enter these corrections which were made in an Examiner's amendment. Since the errors appear to be on the part of the United States Patent Office, there should be no charge.

9/20/06
Date

Respectfully submitted,
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CERTIFICATE OF CORRECTION

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PATENT NO.: 6821829
APPLICATION NO: 09/592349
DATE: 11/23/2004
INVENTOR(S): PEATMAN, WILLIAM C.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

In Column 8, After Line 36, Claim No. 11:

Insert "forming a dielectric layer over the gate contact, the remaining first portion of the undoped gallium arsenide capping layer and the exposed portion of the surface of the delta-doped heteroepitoxial semiconductor substrate;"

MAILING ADDRESS OF SENDER (Please do not use customer number below)

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